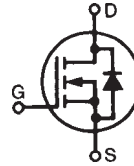


# PolarHV™ Power MOSFET

IXTA 16N50P  
IXTP 16N50P  
IXTQ 16N50P

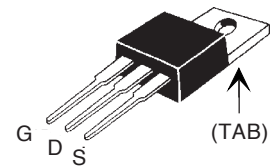
$V_{DSS} = 500 \text{ V}$   
 $I_{D25} = 16 \text{ A}$   
 $R_{DS(on)} = 400 \text{ m}\Omega$

N-Channel Enhancement Mode

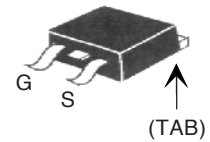


Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	500	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1 \text{ M}\Omega$	500	V
$V_{GSM}$		$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	16	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	48	A
$I_{AR}$	$T_C = 25^\circ\text{C}$	16	A
$E_{AR}$	$T_C = 25^\circ\text{C}$	25	mJ
$E_{AS}$	$T_C = 25^\circ\text{C}$	1000	mJ
$dv/dt$	$I_S \leq I_{DM}$ , $di/dt \leq 100 \text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ , $R_G = 10 \Omega$	10	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	300	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6 mm (0.062 in.) from case for 10 s Maximum tab temperature for soldering TO-263 package for 10s	300 260	$^\circ\text{C}$ $^\circ\text{C}$
$M_d$	Mounting torque (TO-220)	1.13/10	Nm/lb.in.
Weight	TO-220	4	g
	TO-263	3	g
	TO-3P	5.5	g

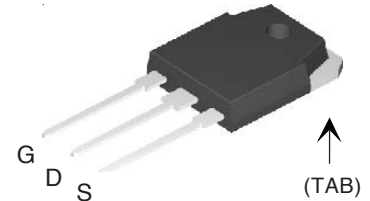
TO-220 (IXTP)



TO-263 (IXTA)



TO-3P (IXTQ)



G = Gate      D = Drain  
S = Source    TAB = Drain

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_{DSS}$	$V_{GS} = 0 \text{ V}$ , $I_D = 250 \mu\text{A}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \mu\text{A}$	3.0		5.0 V
$I_{GSS}$	$V_{GS} = \pm 20 \text{ V}_{DC}$ , $V_{DS} = 0$			$\pm 10 \text{ nA}$
$I_{DSS}$	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$ $T_J = 125^\circ\text{C}$			5 $\mu\text{A}$
				50 $\mu\text{A}$
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$ , $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \mu\text{s}$ , duty cycle $d \leq 2 \%$			400 $\text{m}\Omega$

## Features

- International standard packages
- Unclamped Inductive Switching (UIS) rated
- Low package inductance  
- easy to drive and to protect

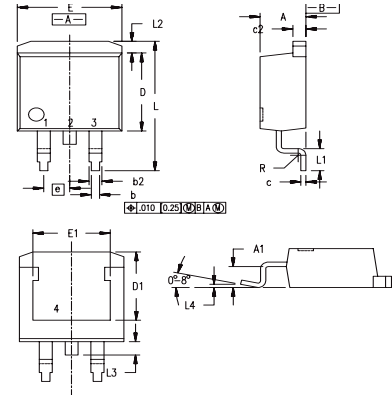
## Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values		
		$(T_J = 25^\circ\text{C}, \text{ unless otherwise specified})$		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 20\text{ V}; I_D = 0.5 I_{D25}$ , pulse test		16	S
$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		2250	pF
$C_{oss}$			240	pF
$C_{rss}$			12	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = I_{D25}$ $R_G = 18\ \Omega$ (External)		23	ns
$t_r$			25	ns
$t_{d(off)}$			70	ns
$t_f$			22	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$		43	nC
$Q_{gs}$			15	nC
$Q_{gd}$			12	nC
$R_{thJC}$	(TO-220) (TO-3 P)			0.42 K/W
$R_{thCK}$			0.25	K/W
$R_{thCK}$			0.21	K/W

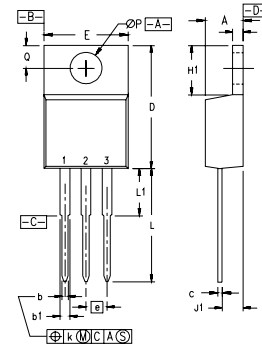
Symbol	Test Conditions	Characteristic Values		
		$(T_J = 25^\circ\text{C}, \text{ unless otherwise specified})$		
		Min.	typ.	Max.
$I_s$	$V_{GS} = 0\text{ V}$			16 A
$I_{SM}$	Repetitive			64 A
$V_{SD}$	$I_F = I_s, V_{GS} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.5 V
$t_{rr}$	$I_F = 16\text{ A}$ $-di/dt = 100\text{ A}/\mu\text{s}$		400	ns

### TO-263 (IXTA) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	.160	.190
A1	2.03	2.79	.080	.110
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.46	0.74	.018	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	7.11	8.13	.280	.320
E	9.65	10.29	.380	.405
E1	6.86	8.13	.270	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.38	0	.015
R	0.46	0.74	.018	.029

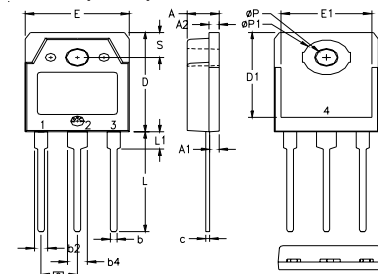
### TO-220 (IXTP) Outline



Pins: 1 - Gate 2 - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

### TO-3P (IXTQ) Outline



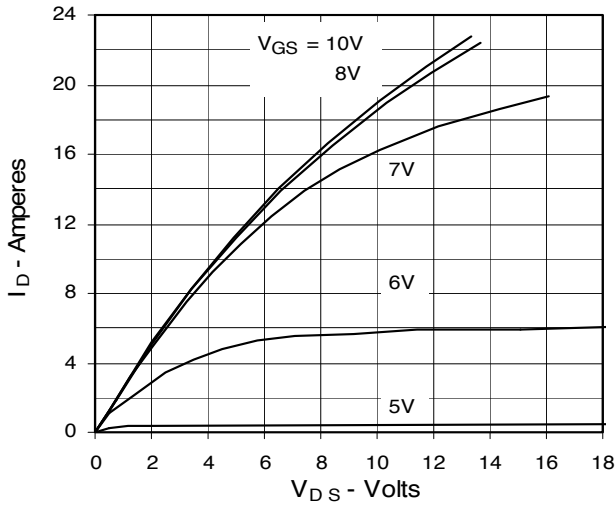
1 - GATE  
2 - DRAIN (COLLECTOR)  
3 - SOURCE (EMITTER)  
4 - DRAIN (COLLECTOR)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.193	4.70	4.90
A1	.051	.059	1.30	1.50
A2	.057	.065	1.45	1.65
b	.035	.045	0.90	1.15
b2	.075	.087	1.90	2.20
b4	.114	.126	2.90	3.20
c	.022	.031	0.55	0.80
D	.780	.791	19.80	20.10
D1	.665	.677	16.90	17.20
E	.610	.622	15.50	15.80
E1	.531	.539	13.50	13.70
e	.215 BSC		5.45 BSC	
L	.779	.795	19.80	20.20
L1	.134	.142	3.40	3.60
ØP	.126	.134	3.20	3.40
ØP1	.272	.280	6.90	7.10
S	.193	.201	4.90	5.10

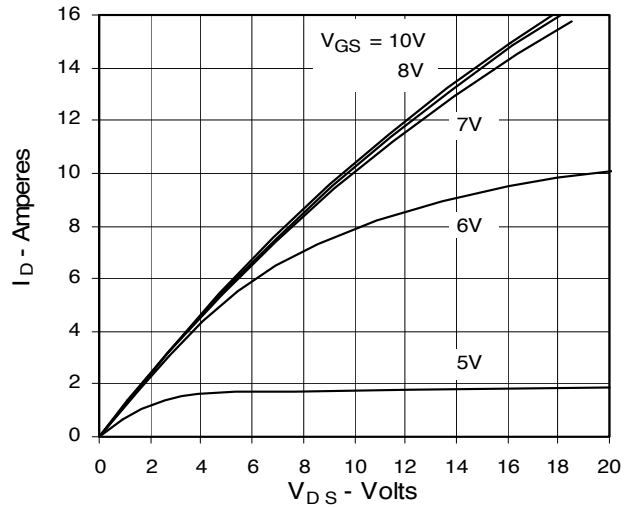
All metal area are tin plated.

IXYS reserves the right to change limits, test conditions, and dimensions.

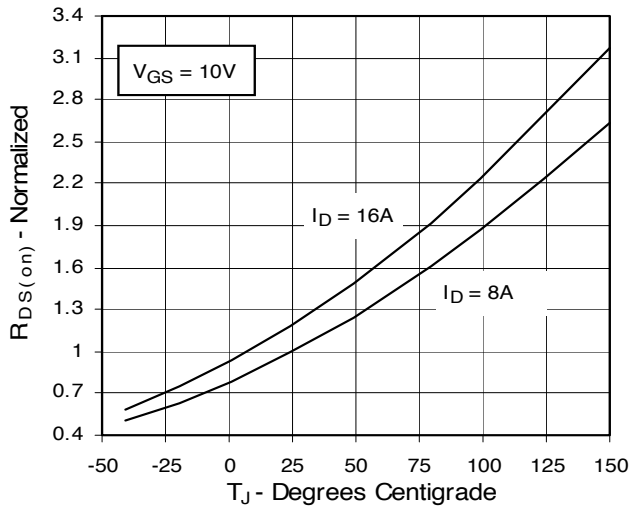
**Fig. 1. Output Characteristics**  
@ 25°C



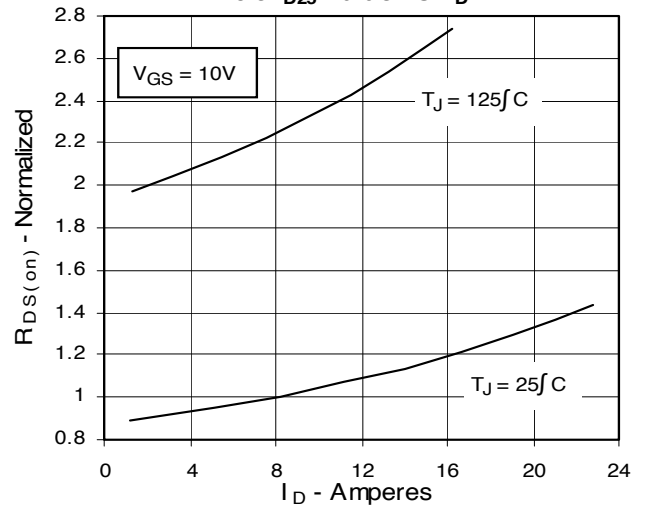
**Fig. 2. Output Characteristics**  
@ 125°C



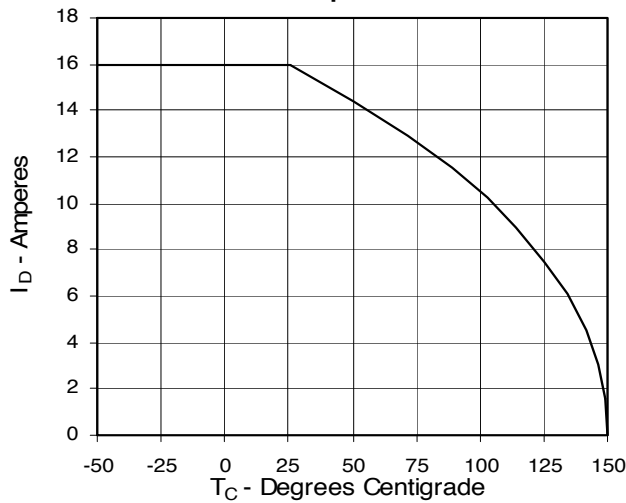
**Fig. 3.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$  Value vs. Junction Temperature**



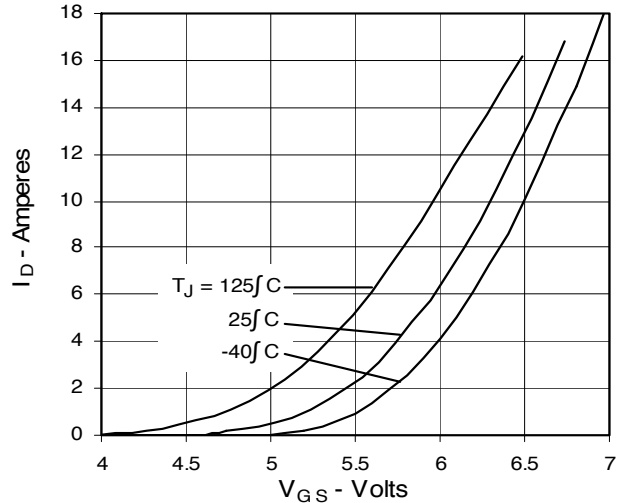
**Fig. 4.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$  Value vs.  $I_D$**



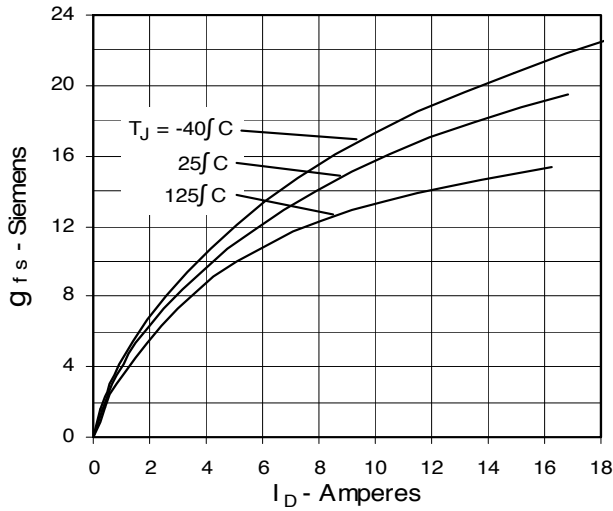
**Fig. 5. Drain Current vs. Case Temperature**



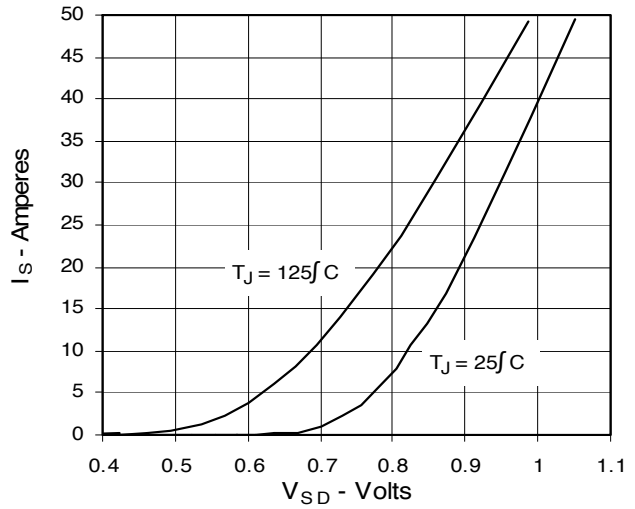
**Fig. 6. Input Admittance**



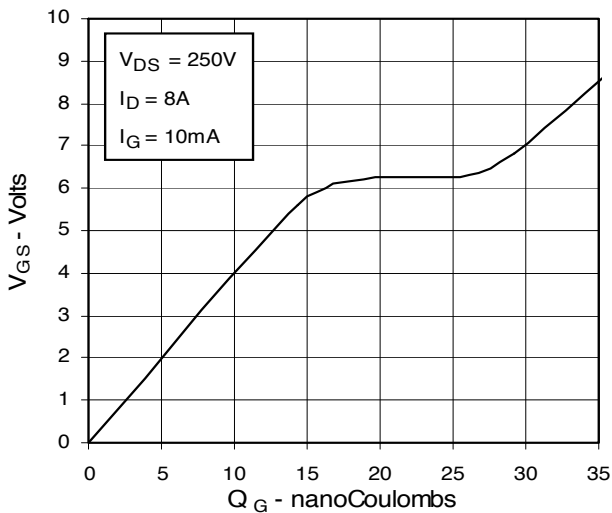
**Fig. 7. Transconductance**



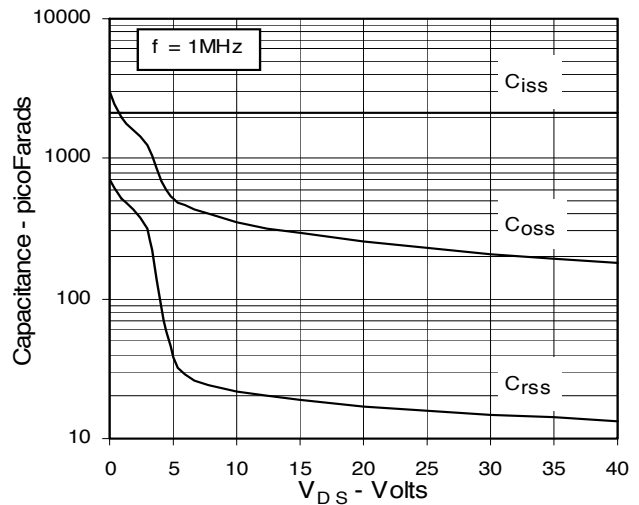
**Fig. 8. Source Current vs. Source-To-Drain Voltage**



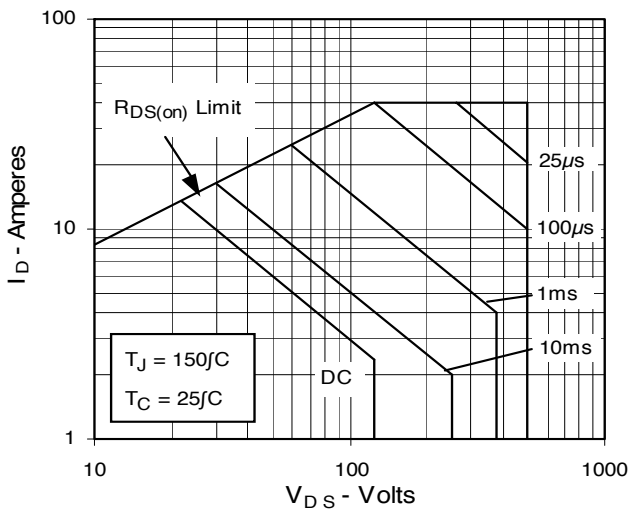
**Fig. 9. Gate Charge**



**Fig. 10. Capacitance**



**Fig. 11. Forward-Bias Safe Operating Area**



**Fig. 12. Maximum Transient Thermal Resistance**

